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Article

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GeI₂ Additive for High Optoelectronic Quality CsPbI₃ Quantum Dots and Their Application in Photovoltaic Devices

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Abstract

Triethylphosphine (TOP)-based syntheses of CsPbI₃ perovskite quantum dots (QDs) yield unprecedented high photoluminescence quantum yield (PL QY), lower Stokes shifts, and longer carrier lifetimes due to their enhanced crystallinity. This synthetic route relies on a heavily Pb-rich condition or a large Pb:Cs molar ratio in precursor solution to produce QDs with appropriate stoichiometry as well as to guarantee a good colloidal stability. The high Pb condition is achieved by a high concentration of PbI₂ prepared in TOP. Here we find such Pb-rich strategies can be avoided by

providing additional iodine ions using other metal halide salts. In particular GeI_2 , which contrary to PbI_2 , readily dissolves in TOP. CsPbI_3 QDs prepared using $\text{PbI}_2/\text{GeI}_2$ combination show near-unity PL QY and improved chemical stability compared to the previous synthetic route. Furthermore we find no sign of Ge incorporation in the QDs (compositionally or energetically). The ensuing QD solar cells deliver power conversion efficiency of 12.15% and retain 85% of its peak performance after storage over 90 days. The $\text{PbI}_2/\text{GeI}_2$ dual-source iodine synthetic approach presented here represents a more rational and robust route to high-quality CsPbI_3 QDs.

Introduction

Perovskites of the general formula ABX_3 ($\text{A} = \text{CH}_3\text{NH}_3^+$, $\text{CH}_3(\text{NH}_2)_2^+$, and Cs^+ , $\text{B} = \text{Pb}^{2+}$, Sn^{2+} , Cu^{2+} , Bi^{3+} , and Sb^{3+} , $\text{X} = \text{Cl}^-$, Br^- , and I^-) are an important class of materials that have been extensively studied as promising candidates for light-harvesting as well as light-emitting applications.¹⁻⁶ These materials, and mainly the all-inorganic CsPbI_3 compound, have recently attracted intense research interest due to their suitable bandgap of 1.73 eV and improved phase/thermal stability in contrast to organic-inorganic hybrid counterparts.⁷⁻¹¹ However, the corner shared perovskite phase of CsPbI_3 is unstable in bulk as it prefers to change to the non-perovskite delta orthorhombic phase at room temperature.¹²⁻¹⁷ To overcome this notable phase instability, CsPbI_3 perovskite has been processed into quantum dots (QDs). It was found that restricting the physical dimension of these semiconductor crystallites to a few nanometers greatly improves phase stability due to the large contribution of surface energy.^{12, 15} Meanwhile, it also brings new attractive features, such as large spectral tunability and outstanding light emitting properties. Many groups across the world are now focused on synthesizing high-quality perovskite QDs and exploring their potential use in various applications.^{13, 15, 18-30}

So far, there are several colloidal synthetic protocols established which lead to the formation of highly crystalline and size-tunable CsPbI_3 QDs.^{14-15, 19, 28, 31-33} Among them, trioctylphosphine (TOP)-based synthetic methods recently proposed by our

group represent an efficient alternative to the traditional ways, whose QD product can approach near-unity photoluminescence quantum yield (PL QY) under optimized conditions due to their enhanced crystallinity.²⁸ However, our understanding of the parameters governing the successful synthesis of these nanocrystals is still very limited, a direct consequence of which is that, following those traditional synthetic approaches, an excessively high PbI_2 dissolved in TOP is often empirically determined. But on the other hand, lowering the use of PbI_2 to a certain degree will not lead to the successful synthesis of high-quality QDs with excellent colloidal stability and crystal quality. Such Pb-rich requirement brings daunting inconvenience and also causes a lot of toxic Pb waste.^{28, 34} Unfortunately, the reason why excess PbI_2 is necessary and whether the use of PbI_2 can be reduced still remains unknown. The above questions drive us to gain more insight in the underlying precursors and reactions for the formation of CsPbI_3 QDs.

In this report, we elaborate on the synthesis of CsPbI_3 QDs, finding that Pb-rich conditions are actually not necessary for producing high-quality CsPbI_3 QDs and instead the excess iodide ions are what play a key role in stabilizing the final QDs. The reason why the traditional protocols as well as our TOP method need such a Pb-rich condition is because in these routes PbI_2 serves as the sole source of iodide ions, an excess PbI_2 is thus required to provide sufficient iodide ions to deactivate the reaction between Cs-oleate and CsPbI_3 QDs, the main detrimental process responsible for the failure of QD synthesis conducted under Cs-rich conditions. Based on the above guidelines, a new synthetic avenue was proposed which involves the use of other iodine salts, specifically here we use GeI_2 , to serve as the robust source of iodide ions, thereby the demand for PbI_2 is greatly relieved. Other halide precursors such as ZnX_2 , InX_3 , NH_4X , and benzoyl halides have also been previously demonstrated for the synthesis of CsPbX_3 , to improve PL QY and chemical stability of the CsPbX_3 QDs,³⁵⁻³⁸ however, in these reports the Pb concentration (or Pb/Cs molar ratio) is still excessively high. We show here that use of metal halides which readily dissolve in TOP, removes the requirement that Pb must be in excess. This facilitates QD synthesis and reduces the amount of unreacted Pb-containing

precursors. Experimental results suggest that Ge is not incorporated into CsPbI₃ lattice, and hence does not affect the intrinsic properties of the resulting QDs. CsPbI₃ QDs prepared herein using PbI₂/GeI₂ precursor combination maintain a high crystalline quality with near-unity PL QY. Furthermore, they show better chemical stability than QD synthesized using only excessive PbI₂. We fabricate CsPbI₃ QD solar cells which exhibit power conversion efficiency (PCE) of 12.15% and retain 85% of its peak performance after storage in dry air over 90 days, showing great promise for practical use.

Results and Discussion

In TOP-based route to synthesizing CsPbI₃ QDs, PbI₂ dissolved in 2.5 mL TOP (0.6~1 mol/L, M) is rapidly injected into an octadecene solution containing Cs-oleate (0.75 mmol) at 120~180 °C.²⁸ CsPbI₃ QDs are generated presumably by the following reaction processes:

Reaction 1 produces the initial CsI crystals, which serve as the seed core for the formation of CsPbI₃ QDs by reacting with PbI₂ (*i.e.*, Reaction 2). Overall, the formation of CsPbI₃ QDs can be described as follows:

Accordingly, for complete reaction of both precursors, the Pb/Cs molar ratio must be ~1.5. However, empirically, for the sake of better colloidal stability and improved optoelectronic characteristics (such as unity PL QY), a Pb/Cs molar ratio of 2~2.6 in reaction mixture is typically used.²⁸ In fact, in previous traditional routes, this ratio is even higher (~4), which means that in both routes the PbI₂ is largely excessive, *i.e.*, the Pb-rich condition.^{12, 15} In such conditions, unreacted PbI₂ and Pb-related byproducts remain.³⁴ For Pb/Cs molar ratio < 1.5, *i.e.*, the Cs-rich (or Cs-oleate-rich) condition, one may intuitively think the synthesis can also proceed with some Cs-related byproducts. However, unlike the Pb-rich conditions, reactions conducted at Pb/Cs molar ratio less than 1 do not lead to the formation of CsPbI₃ QDs and only a

white turbid suspension is obtained (see Figure S1a-b). Although Pb/Cs molar ratio at 1.1~1.5 can yield CsPbI₃ QDs, they decompose or transform quickly within a short period of time (5~10 min). The above facts point to a prerequisite in the synthesis that PbI₂ must be in excess.

In order to identify the mechanism behind the decomposition with lowered Pb/Cs molar ratios, we simulate a scenario using a neat CsPbI₃ QD solution which was prepared by a previous recipe.²⁸ As shown in Figure S1c-d, the neat CsPbI₃ QD solution gradually changes from red clear to white turbid with the addition of extra Cs-oleate, indicating the decomposition or transformation of the CsPbI₃ QDs. X-ray diffraction (XRD) technique was employed to monitor the substance produced at different stages. As shown in Figure S2, upon the addition of Cs-oleate, Cs₄PbI₆ crystal was first identified. A possible reaction for this can be written as follows:

Further, with the increase in the addition of Cs-oleate, CsI precipitated out (Figure S3), which can be rationalized by the following reaction:

Bearing these in mind, we now turn to the formation process of CsPbI₃ QDs (Reaction 1-2). If the above competitive reactions (Reaction 4, 5) take place in parallel to Reaction 1-2 and at a considerable rate, it would be indeed imperative to dissolve enough PbI₂, the sole source of iodine, to release sufficient iodide ions (I⁻) to accelerate the reaction with Cs-oleate through: I⁻ + Cs⁺ = CsI, *i.e.*, the essence of Reaction 1, so as to alleviate the reaction between Cs-oleate and CsPbI₃ QDs.

One conclusion from the above deduction can be also drawn that the excess Pb²⁺ ions are in fact not essential for obtaining stable CsPbI₃ QDs as long as the iodide ions are sufficient to balance (or to consume) the excess Cs-oleate. In order to verify this notion, we design an I-rich environment, where Pb²⁺ ions are set at a very low concentration. To do so, a mixture of GeI₂ and PbI₂ dissolved in TOP is prepared. The choice of GeI₂ to serve as the additional source of iodine is mainly because that superior to PbI₂, GeI₂ precursor solution with a high concentration can be readily

prepared in TOP. For example, dissolving 2 mmol of GeI_2 in 2.5 mL of TOP only takes 1~2 hours. The faster dissolution of GeI_2 in TOP may benefit from its stronger coordination ability with TOP due to acceptor and donor interaction.³⁹

Figure 1. (a) Steady-state UV-vis absorption and PL emission spectra of the prepared QD solution. Full width at half maximum (FWHM) of the PL spectrum was about 33 nm. The inset shows a picture of a QD solution. (b) XRD patterns of the dried QD solution and a reference pure cubic-phase CsPbI_3 crystal. (c) HRTEM image of the QD sample. The inset graph shows statistical analysis of the size distribution while the inset image shows a zoomed-in image of the nanocrystals with well-resolved lattice fringes. (d) PL emission spectra of the QDs with different I/Br ratios synthesized at 180 °C (FWHM: 32~37 nm). The inset shows pictures of the two representative QD solutions taken under ultraviolet light.

Thus, a new synthetic approach using $\text{GeI}_2/\text{PbI}_2$ precursor mixture to high-quality CsPbI_3 QDs is described as follows: Briefly, 2.5 mL of TOP dissolved with 2 mmol

of GeI_2 and 0.5 mmol of PbI_2 is swiftly injected into an octadecene solution (12 mL) containing 0.75 mmol of Cs-oleate at 180 °C with vigorous stirring. Immediately upon injection, the solution changes from colorless to deep red, indicating nucleation and subsequent growth of the colloidal nanoparticles. The reaction was allowed to proceed for ~4 s after which the flask was rapidly cooled to room temperature. After synthesis, the QDs are washed with methyl acetate (MeOAc) to remove unreacted precursor and other synthesis products to yield a clean solution of CsPbI_3 QDs (more experimental details can be found in Supporting Information). We note the formation of Cs_4PbI_6 in the raw solution but these are mostly removed during this purification process (more details about the removal of Cs_4PbI_6 in the raw solution can be found in Figure S4, Supporting Information). It is important to mention that the added PbI_2 in TOP is now decreased to 0.2 M, which is significantly lower than that previously used (0.6~1 M), and the Pb/Cs molar ratio in reaction mixture is decreased to 0.66. We emphasize this is also the minimum value that CsPbI_3 QDs can be successfully produced, below which no CsPbI_3 QDs can be obtained (see Figure S5). Figure 1a shows UV-vis absorption and PL emission spectra of the resulting QDs. The sharp optical absorption edge (~670 nm) along with the narrow PL emission (~677 nm) suggest the successful synthesis of the CsPbI_3 QDs. XRD measurement was performed to examine crystal structure and phase purity of the resulting colloids. For XRD measurement, samples were prepared by dropping the purified solution on a glass substrate and dried by spin-casting. The main diffraction peaks at 14°, 20°, and 28.6° shown in Figure 1b confirm cubic-phase CsPbI_3 product. Figure 1c shows a representative high-resolution transmission electron microscopy (TEM) image of the purified sample, where uniform cubic-shaped dots (average size of ~12 nm) with well-resolved lattice fringes (interplanar spacing of 0.62 nm) can be clearly identified, indicating highly crystalline structure of the resulting CsPbI_3 QDs.

The above experimental results unambiguously show that CsPbI_3 QDs can be successfully synthesized even under a low concentration of PbI_2 (3 to 4-fold decrease as compared with before) by using a combined Ge/Pb precursor. One additional merit using the Ge salt additives is that it now enables preparation of CsPbX_3 QDs with

various halide compositions, and because of which a wider range of luminescence emission can be obtained (see Supporting Information for more synthetic details). Indeed, the efficacy of the previous strategy employing PbX_2 alone for the synthesis of different halide compositions is largely limited because of the extremely low solubility of PbBr_2 in TOP ($\ll 0.1$ mol/L). In contrast, Ge halide compounds can provide sufficient bromide ions to the reaction due to their higher solubility in TOP. Figure 1d displays that CsPbX_3 QDs prepared using different $\text{PbI}_2/\text{GeI}_2/\text{GeBr}_2$ combinations exhibit photoluminescence from 520 to 677 nm and show bright fluorescence under ultraviolet light (the detailed synthesis conditions for each PL spectrum were given in Table S1).

Figure 2. (a) Wide-scan XPS spectra of the resulting QDs. Inset displays an enlarged view from 0~60 eV. (b) TEM image and EDX microanalysis mapping of a single QD. The scale bar represents 10 nm.

Using the dual halide source precursor ($\text{GeI}_2/\text{PbI}_2$), we question whether the Ge element is present in the final QDs. Previous studies using Zn salts in hot-injection synthesis reported no incorporation of Zn^{2+} in their samples.³⁷⁻³⁸ We therefore suspect Ge to behave similarly, but nonetheless probe to see if we can find evidence of it. To examine the composition and valence state of the constituent elements, X-ray photoelectron spectroscopy (XPS) measurement was carried out. As shown in Figure 2a, XPS peaks assignable to Cs(I) 3d, Pb(II) 4f, and I(I) 3d can be clearly identified. However, Ge signals typically appear in the range of 25~35 eV,⁴⁰ and no clear XPS

peaks can be resolved in that range. This indicates that the washed QD product contains negligible amount of the Ge element. TEM-energy dispersive X-ray microanalysis (TEM-EDX) was further conducted to confirm this result. As can be seen from Figure 2b, Cs, Pb, and I elements are homogeneously distributed throughout the QD while for the Ge element, EDX does not have the necessary signal to noise ratio to be considered processible, confirming that Ge element is indeed not present in the final QDs and the resulting colloids are basically CsPbI₃ QDs. In order to investigate the potential role of GeI₂ in the synthesis besides the identified role of I⁻ source, we then carried out XPS measurement to study the chemical state of Ge in the solution after reaction. Details about sample preparation can be found in caption of Figure S6. Figure S6 shows that binding energy of Ge 3d after synthesis is not significantly changed as compared to that of the as-bought GeI₂ powder, indicating that the chemical state of Ge is not affected during reaction. Therefore, from the above results, we can safely conclude that GeI₂ serves only as a source of I⁻ during formation of CsPbI₃ QDs.

Figure 3. (a) Evolution of the PL QY of the prepared QD solutions over storage time.

Dotted red: $\text{PbI}_2/\text{GeI}_2$ -produced CsPbI_3 QDs. Dotted blue: excessive PbI_2 -produced QDs (Ref. 28). Both QDs were synthesized at 180 °C, washed once with 122 mL of MeOAc and stored in a sealed bottle with air at room temperature. (b) Absorption coefficient of the CsPbI_3 QDs prepared using $\text{PbI}_2/\text{GeI}_2$ combination method versus only PbI_2 (Ref. 28) (particle size ~12 nm). (c) Time-resolved PL decay curves of the CsPbI_3 QDs. Pump intensity and wavelength are 0.29 mW and 532 nm, respectively. (d) TA kinetic traces of the CsPbI_3 QDs. TA spectra were recorded with excitation wavelength of 470 nm, excitation intensity of 1 $\mu\text{J}/\text{cm}^2$, and probe wavelength of ~670 nm. The inset shows TA spectra recorded at different delay times.

Photophysical properties of the resulting CsPbI_3 QDs were first evaluated by measuring their PL QYs using a commercial Hamamatsu setup (details about the measurement principle can be found in Figure S7). Amazingly, high PL QY of nearly 100% is achieved for these CsPbI_3 QDs prepared under such a low PbI_2 concentration (A histogram of the PL QY values for 14 batches of syntheses is presented in Figure S8). This means that the intrinsic decay channel of the excited states in these QDs is also nearly completely radiative. More importantly, QDs show PL QY of $99\pm 2\%$ even after 1 month storage (Figure 3a). In contrast, those CsPbI_3 QDs prepared using only excessive PbI_2 as described in our previous method (Ref. 28) can only maintain PL QY of $100\pm 2\%$ for the first 9 days and dropped to $\sim 85\pm 2\%$ after storage for 1 month. In order to gain more insight about the superior photophysical properties of the QDs produced by $\text{PbI}_2/\text{GeI}_2$ method, XPS measurement was carried out. XPS measurements have been widely used to assess the surface modification of the QDs⁴¹ and to understand the mechanism of PL enhancement. Quantitative XPS analysis for QDs produced by $\text{PbI}_2/\text{GeI}_2$ method indicates a I/Pb ratio of 4.0 ± 0.2 , which is higher than that of the stoichiometry in the bulk (I/Pb ratio = 3) (note that the measured QD samples have been sufficiently purified with MeOAc after synthesis). The excess iodine may come from the capping ligands on QD surface, oleylammonium iodide, which helps to passivate the surface defects.^{11, 27, 42} Further, as a comparison, we carried out quantitative XPS analysis on QDs prepared by PbI_2 -only method, I/Pb

ratio turns out to be 3.3 ± 0.2 , which is lower than that prepared by $\text{PbI}_2/\text{GeI}_2$ method. The stable high PL QY makes the synthesized QDs highly suitable for many applications, including biological labeling, LEDs, photovoltaics, and lasers. Further, small Urbach energy (E_U) ~ 19 meV calculated by a reference method is also obtained from Figure 3b, which is close to that of the QDs prepared by PbI_2 -based method of similar particle size. The measured low E_U value is a strong sign that the QDs suffer less from impurities, inherent structural disorders, and electron-phonon interaction in their light-absorption process.⁴³⁻⁴⁵ PL decay measurement probing the PL maximum (~ 677 nm) shows these 12 nm- CsPbI_3 QDs exhibit spectrally uniform single-exponential decay with a 22 ns time constant (Figure 3c), which implies a single recombination channel across the entire QD ensemble. The above results thus confirm that lowering the use of PbI_2 does not necessarily impair the intrinsic properties of CsPbI_3 QDs, instead, the resulting QDs can still maintain a low level of electronic disorder and/or defect density, and therefore an excellent crystalline nature. However, unlike the CsPbI_3 QDs, it should be mentioned that the prepared CsPb(I/Br)_3 QDs using $\text{PbI}_2/\text{GeBr}_2$ combination do not show PL QY as high as $100 \pm 2\%$. In fact, PL QY of the CsPb(I/Br)_3 QDs significantly decreased from $100 \pm 2\%$ to $40 \pm 2\%$ with the increase in Br content. It should be mentioned that the decrease of PL QY of the perovskite QDs when using mixed halides is not exclusive to this work. For example, in Ahmed *et al.*'s report, the directly synthesized CsPbBr_3 and CsPbI_3 QDs exhibit PL QY of $\sim 30\%$ and $\sim 40\%$, respectively, while that of $\text{CsPbI}_{3-x}\text{Br}_x$ is $10 \sim 13\%$.¹¹ In our own experience following a universal synthetic method,¹⁵ under optimal conditions, we can achieve PL QY of $\sim 90\%$ for CsPbI_3 QDs and $\sim 80\%$ for CsPbBr_3 QDs, however, PL QY of $\text{CsPbI}_{3-x}\text{Br}_x$ is typically lower, being $50 \sim 70\%$. Similar observation is also reported by Liu *et al.*⁴⁶ These experimental results indicate that the mixed halide source synthesis could induce remarkable formation of lattice/surface defects that would lead to deterioration of the optical properties of the QDs.

The successful application of GeI_2 in the synthesis of high-quality CsPbI_3 QDs drives us to explore the efficacy of the other metal halides, such as CuI , HgI_2 , ZnI_2 ,

AgI, NH₄I, and SrI₂. We found that all these studied metal halides can be readily dissolved in TOP with a high concentration (~0.8 M) except for SrI₂ (< 0.1 M) and NH₄I (< 0.2 M). However, among these dissoluble metal halides, only ZnI₂ can lead to the successful synthesis of CsPbI₃ QDs (Figure S9). Yet compared to QD prepared with GeI₂, the ZnI₂-based CsPbI₃ QDs show lower PL QY (~50±2%) and less colloidal stability. The reason behind this observation is still under investigation; however, we consider the difference in the ability of these metal salts to release reactive iodide ions could probably account for these. The above fact also indicates that the compensatory halide precursor used in TOP route is highly selective.

Femtosecond transient absorption (TA) measurement was performed to elucidate the mechanism underlying the superb photophysical properties of the resulting CsPbI₃ QDs prepared using PbI₂/GeI₂ combination. Upon band gap excitation of the QDs with light pulse, one can see bleaching signal (absorption changes $\Delta A < 0$) in its TA spectrum, which corresponds to state filling by electrons and/or holes in the QDs.⁴⁷ In the absence of charge transfer between QDs or a charge acceptor, the recovery of the transient bleach or depletion of the absorption signal near band gap of the QDs represents the disappearance of the photogenerated electrons and/or holes *via* charge recombination and trapping processes within a single QD.⁴⁸⁻⁴⁹ Therefore, TA measurement can serve as a measure of the trap states in the QDs. But before carrying out analysis of trap states using TA measurement, Auger recombination in CsPbI₃ QDs is first studied and eliminated because the Auger recombination time scale could potentially overlap with that of the charge trapping process and tend to complicate the discussion.⁵⁰⁻⁵³ Figure S10 shows the dependence of the normalized TA decays on pump excitation intensities for the measured QDs. It is clearly seen that the decay process becomes fast when the pump intensity is larger than 2 $\mu\text{J}/\text{cm}^2$. This observation indicates the presence of Auger recombination process in QDs under the high pump intensity excitation.⁵³ When the pump intensity is smaller than 2 $\mu\text{J}/\text{cm}^2$, we found the fast decay process disappeared and the waveforms of the TA responses overlapped with each other very well within 1 ns when they were normalized at the peak intensity. This means the Auger recombination process is negligible under such

low pump intensity excitation. Therefore, in the following, for the TA measurements, QD samples will be excited with a safe pump intensity of $1 \mu\text{J}/\text{cm}^2$ to eliminate the potential interference of Auger process. Figure 3d shows TA response of the CsPbI_3 QDs measured with pump intensity of $1 \mu\text{J}/\text{cm}^2$, where no significant decay can be resolved in the initial 1 ns time scale, suggesting the negligible electron or hole trapping pathways in the QDs.

In order to apply these high-quality colloidal QDs into high-performance photovoltaics or light emitting diodes, it is typically required to process them into compact thin films so as to enable an efficient charge transfer between nanoparticles. Here, QD compact thin films with a controllable thickness were prepared by a modified deposition process, which was initially developed for making high-efficiency CsPbI_3 QD solar cells.^{12, 54} Specifically, in a N_2 -filled glovebox, 100 μL of QD solution ($\sim 60 \text{ mg/mL}$) was first deposited on a fluorine-doped tin oxide (FTO) glass by spin casting at 3600 rpm for 20 s. Then the as-cast QDs were treated 5~6 times with MeOAc, in each treatment, QD surface was flooded with MeOAc, left for ~ 1 s and dried at 3600 rpm for 20 s. The above QD deposition-MeOAc washing process is defined as one cycle of QD deposition and it can be repeated several cycles to produce dense films with a desired thickness. Figure S11a shows a typical cross-section scanning electron microscope (SEM) image of a prepared QD thin film, where a 200-nm-thick compact QD layer can be clearly identified on the FTO substrate. Comparison of the Fourier-transform infrared (FT-IR) spectra of the QD films as cast and after treatment with MeOAc suggests the further removal of the organic species from the QDs, given that those C-H bending vibration peaks at 2853 and 2923 cm^{-1} assignable to the hydrocarbon chains from organics are significantly reduced (Figure S11b).⁴¹

Figure 4. TA kinetic traces of the QD dense films and those dispersed in solution. Excitation wavelength is 470 nm and power intensity is $1 \mu\text{J}/\text{cm}^2$. Solid line shows fit to the TA dynamics.

As mentioned above, free-standing QDs are processed into dense thin films to enable their electrical contact and thus allow an efficient charge transfer between nanoparticles. First evidence of the efficient charge transfer between QDs comes from steady-state PL spectra, from which we can see the intrinsic fluorescence of the QDs was significantly quenched in the films (Figure S12). To obtain direct evidence of the charge transfer and, furthermore, to evaluate the rate of this process, next, again, TA spectroscopy was employed. For TA measurement, QD dense films were prepared on a quartz glass and QDs dispersed in solution were used as reference. Both were excited with wavelength of 470 nm and power intensity of $1 \mu\text{J}/\text{cm}^2$ (Figure S13a shows that under this low power intensity the Auger recombination in QD thin film is negligible). Normalized TA kinetics at the bleach maximum were recorded for each sample as shown in Figure 4. It should be mentioned that the TA bleach maximum of the free QD solution is located at ~ 670 nm, while that of QD thin film sample is located at ~ 685 nm. This red shift may result from some degree of attachment after MeOAc treatment, which results in a decrease in the averaged QD-QD distance and causes a change in the dielectric environment of the surface bound QDs when compared to the solution, and eventually affects the total energy of an exciton confined to the QDs.⁵⁵⁻⁵⁷ It is seen that compared to the non-decay TA kinetic features

observed for those QDs dispersed in solution, TA response of the thin films shows fast decay within 1 ns. This is indicative of charge transfer between QDs. Fitting of the TA response of the QD thin films gives single-exponential decay kinetics (*i.e.*, $A_0 \exp(-t/\tau) + y_0$) with time constant of ~ 50 ps ($A_0 \approx 90\%$) and $y_0 \approx 10\%$. The derived fast decay component thus reveals that the photoexcited charge carriers in QDs can transport between each other with a fast transfer rate (k_{et}) of $0.2 \times 10^{11} \text{ s}^{-1}$ ($k_{\text{et}} = 1/\tau$). It is important to bear in mind, however, that the decay of TA signal can be also related to surface trapping defects with a close lifetime to that of charge transfer since CsPbI₃ QDs have undergone a severe surface treatment with MeOAc during thin film deposition, surface trapping defects can be formed and contribute to decay of TA signal. However, due to their close lifetime constant, it is difficult to quantitatively estimate the contribution of these two different processes to the TA decay. In order to gain more insight into the presence of trap states in QD thin films, we obtained spectro-temporal TA map for CsPbI₃ QD thin films, as shown in Figure S13b. The red shift of the bandedge bleach maximum with time in a spectro-temporal TA map correlates to a certain degree of disorder with energy funnelling towards undesired bandtail states, it can be thus tracked as a sign of trap states below the bandgap.⁵⁸ A very small redshift ~ 3 meV of the transient bleach peak is observed for the investigated CsPbI₃ QD thin film, suggesting a flat energy landscape and a very shallow trap below the bandgap. Given such a shallow trap state reflected here, we consider TA decay near band gap of the QDs is dominated by charge transfer process between QDs.

Figure 5. (a) Cross-sectional SEM image of the fabricated solar cells. (b) Current density-voltage (J - V) curves of the champion QD perovskite solar cells measured under simulated solar illumination of 100 mW/cm². (c) IPCE spectrum and integrated photocurrent density for the best-performing solar cell. (d) Long-term device stability measurement of the solar cells. The unsealed solar cells were kept in a dry cabinet (< 20% relative humidity) in the dark under room temperature and tested regularly in open air with the relative humidity of 30~40%. PCE values were obtained from the reverse scans.

The efficient charge transfer between QDs enabled by the thin films renders these materials extremely suitable for use in thin film solar cells. Hall measurements reveal that the prepared QD thin films exhibit p-type conducting behavior with a carrier concentration of $1.28 \times 10^{13} \text{ cm}^{-3}$ and mobility of 22.95 cm²/Vs. The valence band maximum of the CsPbI₃ QDs about -5.25 eV was revealed by photoelectron yield spectroscopy (PYS) measurement, as shown in Figure S14. Band alignment between the QDs and the other layers is shown in the inset of Figure S14, which demonstrates

an energetically favorable band position for the transfer of the photoexcited electrons and holes from QDs to TiO₂ and Spiro-OMeTAD, respectively. We therefore fabricated CsPbI₃ QD planar solar cells using a thin layer of TiO₂ as the electron-acceptor and Spiro-OMeTAD as the hole-transporting layer (detailed fabrication process can be found in Supporting Information). Figure 5a shows a typical SEM image of the cross section of the fabricated solar cells. The best-performing QD solar cell with an optimal QD layer thickness of ~220 nm tested under ambient conditions delivers a PCE of 12.15% (Figure 5b) with hysteresis behavior shown in Figure S15. This is one of the highest efficiency among all-inorganic perovskite solar cells reported so far. A histogram of the PCE values for 28 samples is presented in Figure S16. Integrating the incident photon conversion efficiency (IPCE) data with the AM 1.5G solar spectrum gives calculated short-circuit current density (J_{sc}) value of approximately 13.5 mA/cm² (Figure 5c), which is in good agreement with the experimental value obtained from J - V measurement. We also examined the long-term stability of the solar cells under dark storage in dry air (room temperature, < 20% relative humidity). As shown in Figure 5d, the PCE of the solar cells as determined from reverse J - V scans increased from its initial value over the course of 60 days and retained 85% of its peak performance after 90 days, showing superior stability in dry air. However, when these QD devices are taken out and exposed to ambient conditions of a typical day-night cycle (~25 °C, relative humidity of 30~40%), the efficiency decreases to ~2.5% (Figure S17a), similar to that reported previously.¹² The main cause of this dramatic drop in efficiency is attributed to the known phase transformation of cubic CsPbI₃ to 2D orthorhombic CsPbI₃. Figure S17b shows that light absorption of the QD film has significantly changed after storage in air for one day, in line with transformation of the phase. We have also fabricated solar cells using CsPbI₃ QDs that were prepared with no GeI₂. PCE and stability of the solar cells are summarized in Figure S18. It is observed that efficiency of the solar cells increased in the first three weeks from ~9.0% to ~9.9%, and decreased to ~9.2% after ~30 days storage in dark dry box. Compared to QD devices prepared with GeI₂, the photovoltaic performance and stability of the solar cells with

no GeI_2 is slightly lower. The reason behind this can be due to a better surface passivation of the QDs produced in $\text{PbI}_2/\text{GeI}_2$ route, as revealed by quantitative XPS measurement for PL QY comparison.

Conclusions

In conclusion, we have presented a new synthetic strategy by introducing GeI_2 as an additional robust source of iodide ions, the use of PbI_2 can be thus greatly reduced, which brings significant advantages, such as less toxic Pb waste, better surface passivation of the QDs, and better reproducibility of the products. The resulting CsPbI_3 QDs synthesized with $\text{PbI}_2/\text{GeI}_2$ precursor combination show near-unity PL QY as well as improved chemical stability, and the ensuing QD solar cells exhibit high PCE over 12%. Therefore, the $\text{PbI}_2/\text{GeI}_2$ dual-source iodine synthesis approach introduced here shall represent a more rational and efficient route to high-quality CsPbI_3 QDs.

Associated Content

Supporting Information

Experimental details, solution picture, XRD, SEM images, PL QY measurement, TA spectra, PL spectra, PYS, J - V curves.

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F.L. synthesized the QDs, C.D., Y.Z., and Q.Z. fabricated devices. All authors contributed to QD or device characterization, analysis, figures, and edits to the manuscript.

Notes

The authors declare no competing financial interest.

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